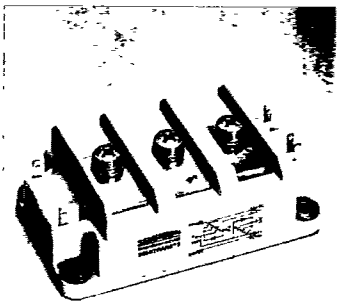
SEMITRANS® 3 NPN
Power Darlington Modules
100 A, 1000 V

T-33-35

SK 100 DB 100 D
SK 100 DAL 100 D



Maximum Ratings

Symbol	Conditions	Values	Units
V_{CEVsus}	I_C = 1 A, V_{BE} = – 2 V	1000	V
V_{CEV}	V_{BE} = – 2 V	1000	V
V_{CBO}	I_E = 0	1000	V
V_{EBO}	I_C = 0	7	V
I_C	D. C.	100	A
I_{CM}	t_p = 1 ms	200	A
$I_F = -I_C$		100	A
I_B		5	A
P_{tot}	T_{case} = 25 °C; per darlington	800	W
T_{vj}		– 40 . . . + 150	°C
T_{stg}		– 40 . . . + 125	°C
V_{isol}	a. c. 50 Hz, r.m.s.	2500~	V

Thermal Characteristics

R_{thjc}	per darlington/per module	0,155/0,077	°C/W
R_{thjc}	per diode/per module	0,65/0,325	°C/W
R_{thch}	per ½ module/per module	0,075/0,038	°C/W

Electrical Characteristics[1)]

			min.	typ.	max.	
I_{CEV}	$V_{CE} = V_{CEV}$, V_{BE} = – 2 V				2	mA
I_{EBO}	I_C = 0, V_{BE} = – 7 V				400	mA
V_{CEsat}[2)]	I_C = 100 A, I_B = 2 A				2,5	V
V_{BEsat}[2)]	I_C = 100 A, I_B = 2 A				3,5	V
h_{21E}[2)]	I_C = 100 A	V_{CE} = 2,8 V	75			
		V_{CE} = 5 V	100			

Switching Characteristics for Resistive Load[1)]

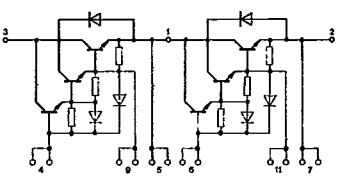
t_{on}	I_C = 100 A			3	µs
t_s	$I_{B1} = -I_{B2}$ = 2 A			15	µs
t_f	V_{CC} = 600 V			3	µs

Inverse Diode Characteristics[1)]

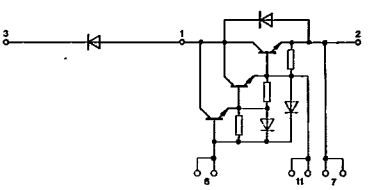
$V_F = -V_{CE}$	$I_F = -I_C$ = 100 A				1,8	V
$I_{FSM} = -I_{Cp}$	sin 180°, 10 ms	1000				A
I_{RM}	$I_F = -I_C$ = 100 A, $-di_F/dt$ = 100 A/µs			38		A
Q_{rr}	V_{BE} = – 3 V, $V_R = V_{CE}$ = 400 V, T_{vj} = 125 °C			19		µC

Mechanical Data

M_1	Case to heatsink	SI units	3		6	Nm
		US units	27		53	lb. in.
M_2	Busbars to terminals	SI units	2,5		5	Nm
		US units	22		44	lb. in.
w				420		g
Case		DB	D 14			
		DAL	D 39			



DB



DAL

Features

- Isolated baseplate (ease of mounting of one or several modules on one heatsink)
- All electrical connections on top (ease of interconnecting of modules with busbars)
- Large clearances and creepage distances
- Parallel connected fast recovery inverse diode
- UL recognized, file no. 63 532

Typical Applications

- Uninterruptible power supplies (UPS)
- DC drives
- AC motor controls
- Brake choppers (DAL)

1) T_{case} = 25 °C unless otherwise stated
2) $t_p \leq$ 300 µs, D ≤ 1,5 %

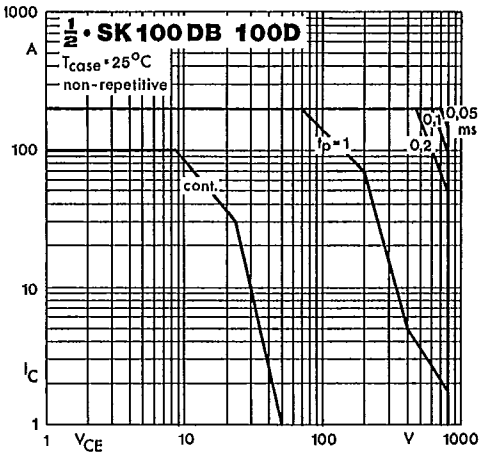


Fig. 1 Forward biased safe operating area (FBSOA)

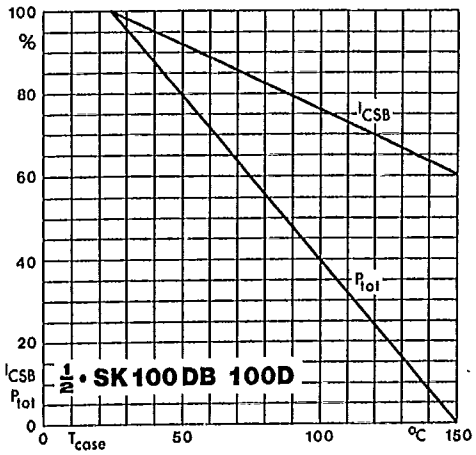


Fig. 2 Shifting the limits of the FBSOA with temperature

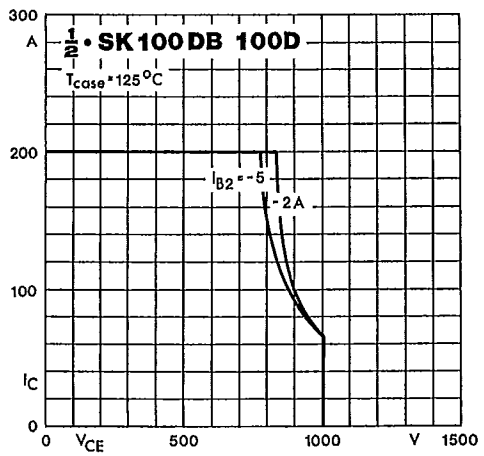


Fig. 3 Reverse biased safe operating area (RBSOA)

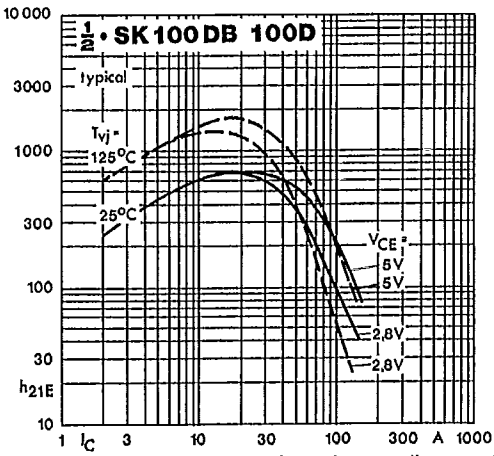


Fig. 4 Forward current transfer ratio vs. coll. current

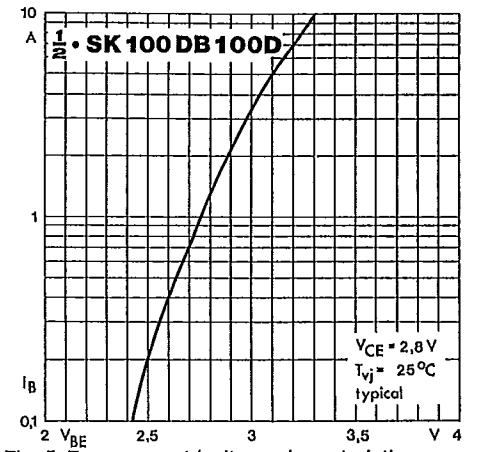


Fig. 5 Base current/voltage characteristic

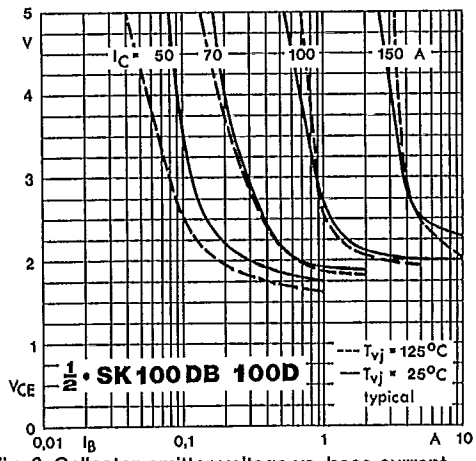


Fig. 6 Collector-emitter voltage vs. base current

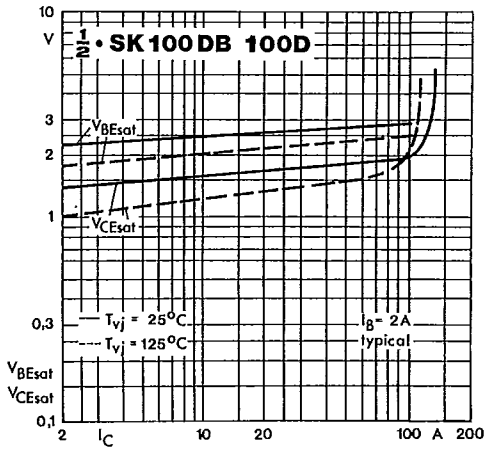


Fig. 7 Saturation voltages vs. collector current

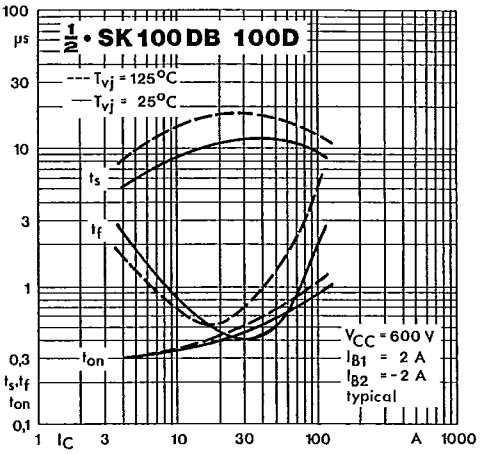


Fig. 8 Switching times vs. collector current

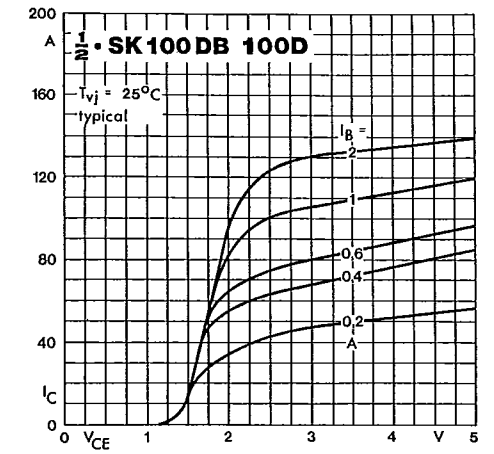


Fig. 9 Collector current/voltage characteristics

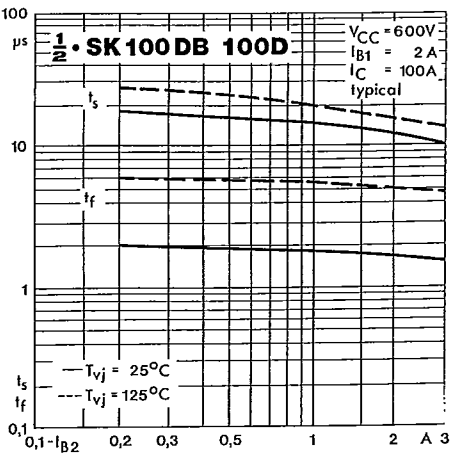


Fig. 10 Turn-off times vs. negative base current

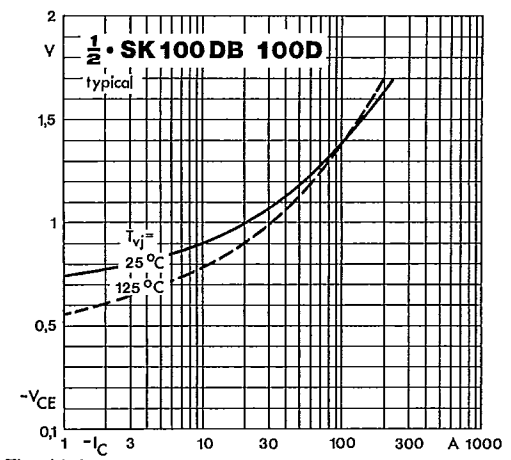


Fig. 11 Inverse diode forward characteristics

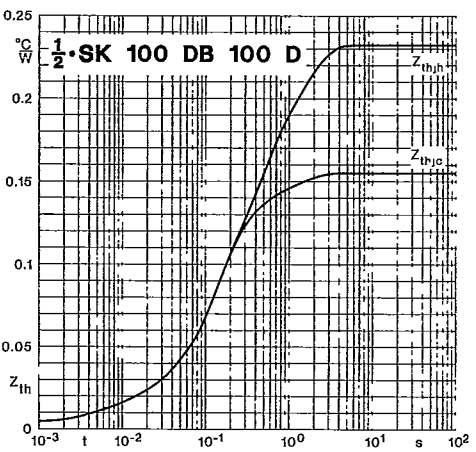


Fig. 12 Transient thermal impedance vs. time

SK 100 DB 100 D

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Case D 14

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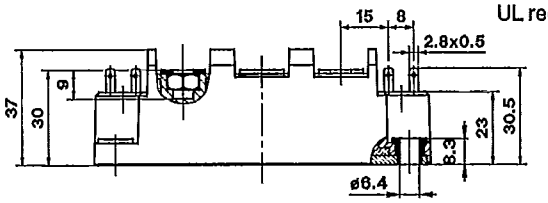

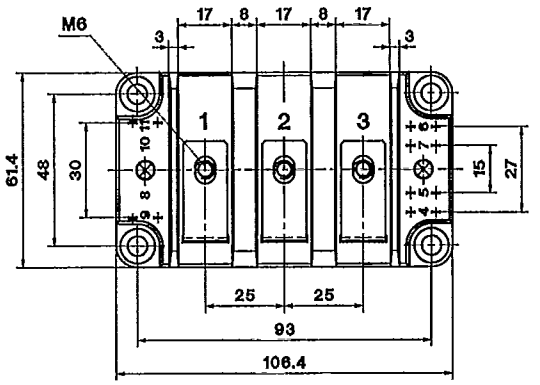

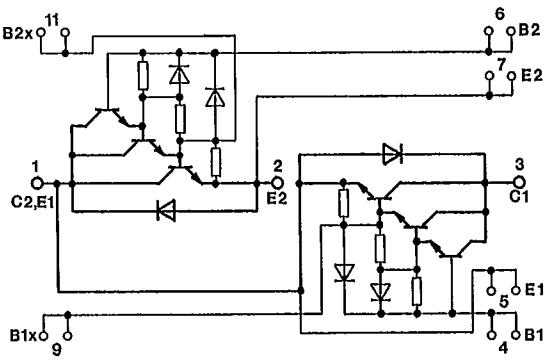

Dimensions in mm

SK 100 DAL 100 D

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